NOTES:
1. CENTERING WITH RESPECT TO FEATURE -A-
   Si DEVICE: WITHIN ±0.015
   Ge DEVICE: WITHIN ±0.010

PRODUCT MARKINGS:

3. SPECIFICATIONS:
   SILICON
   ACTIVE SIZE: 3.5 mm DIA
   WAVELENGTH RANGE: 400 nm TO 1000 nm
   MINIMUM RESPONSIVITY AT 850 nm: 0.45 A/W
   SHUNT IMPEDANCE: 50 Mohms
   NEP (PEAK AND 300Hz): 3.0E-14 (W/Hz1/2) TYPICAL
   GERMANIUM-SC
   ACTIVE SIZE: 2.0 mm DIA
   WAVELENGTH RANGE: 1100-1800 nm
   MINIMUM RESPONSIVITY AT 1300 nm: 0.60 A/W
   SHUNT IMPEDANCE: 80 Mohms
   NEP (PEAK AND 300Hz): 8.0E-13 (W/Hz1/2) TYPICAL
   PACKAGE: TO-5
   WINDOW MATERIAL: BOROSILICATE GLASS

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REV DESCRIPTION DATE APPROVED
0 INITIAL RELEASE 03/21/00 W0/DGF

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Si CATHODE
Ge CATHODE
Si ANODE
Ge ANODE

TOP VIEW

.360 DIA REF -A-
.326 DIA
.250 DIA
.255±.007
.17±.020 TO Si DETECTOR PLANE
.11 (REF) TO Ge DETECTOR PLANE
.4 (NOM) ON A .230 DIA PIN CIRCLE

BOTTOM VIEW

Si CATHODE
Ge CATHODE
Si ANODE